

2022 ATOMIC LAYER PROCESSING MODELLING WORKSHOP

March 15

Time	Title
13:00	<i>Opening talk</i>
13:10	<i>A mechanistic study of the HF pulse in the thermal atomic layer etch of crystalline and amorphous HfO₂</i>
13:25	<i>Atomic-scale modelling applied to the understanding of indium nitride growth by atomic layer deposition methods</i>
13:40	<i>First principles modelling of growth of Al₂O₃-based hybrid films</i>
13:55	<i>Break</i>
14:10	<i>Computational investigation of precursor blocking by aniline inhibitor molecules during area-selective atomic layer deposition</i>
14:25	<i>On the accuracy of density functional theory in prediction of Cu ALD and ALE reaction energies</i>
14:40	<i>Modelling the atomic layer deposition of cobalt and ruthenium on NH_x-terminated Metal Surfaces</i>
14:55	<i>Break</i>
15:20	<i>First-principles framework for surface-assisted dissociative adsorption dynamics</i>
15:35	<i>Film growth modelling through coupling of particle Monte Carlo and Level set methods</i>
15:50	<i>Break</i>
16:15	Tutorial: <i>Reaction network analysis of ALD processes: Is this a true ALD cycles? What rates can be measured?</i>

Speaker
Henrik Pedersen, Linköping University
Rita Mullins, Tyndall National Institute
Giane B. Damas, Linköping University
Arbresha Muriqi, Tyndall National Institute

Ilker Tezsevin, Eindhoven University of Technology
Xiao Hu, Fraunhofer ENAS
Ji Liu, Tyndall National Institute

Mateusz Wlazlo, CB RTP
Joshua Gehre, Fraunhofer ENAS

Raymond Adomaitis, University of Maryland

March 16

08:30	<i>Influence of flow regime on the conformality of atomic layer deposition in lateral channels: simulations with a diffusion-reaction model</i>
08:45	<i>Computational fluid dynamics modeling of spatial atomic layer deposition on microgroove substrates</i>
09:00	<i>Break</i>
09:15	<i>Numerical simulations of atomic layer deposition process</i>
09:30	<i>A call to establish best practice guidelines for reactor-scale simulations</i>
09:50	<i>Break</i>
10:20	<i>Investigating the limitations of plasma-enhanced atomic layer deposition of silver films using lateral high aspect ratio microstructures</i>
10:40	<i>In-situ metrology for atomic layer processes</i>
11:00	<i>Atomic-scale simulation frameworks for ASD</i>
11:20	<i>Break</i>
11:35	<i>Picosun's view on the current state of the art and further development needs in modelling ALD processes</i>
11:55	<i>Validation issues for atomic-scale simulations of atomic layer processing</i>
12:15	<i>Closing</i>

Jorge A. Velasco, Aalto University
Zoushuang Li, Huazhong University

Gizem Ersavas Isitman, Aalto University
Anton Persson, Linköping University

Renaud Leturcq, LIST
Martin Knaut, TU Dresden/ALS Metrology
Umberto Martinez, Synopsys

Tom Blomberg, Picosun Oy
Simon Elliott, Schrödinger
Anton Persson, Linköping University

Main industrial partner:



Main academic partner:

